

ID	Text	IP	Time Stamp
1	Design 1-XX M1-xyun-sym.IN.	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:04
2	1. 1ee-xyun-sym.IN.	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:07
3	contact adj hole near10 passivation and gate adj insulating near10 drain	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:11
931	contact adj hole near10 passivation	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:11
932	contact adj hole near10 gate adj insulating	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:11
46	contact adj hole near10 edge or side; near10 drain adj electrode	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:46
9	((contact adj hole' near10 (passivation' and ((contact adj hole' near10 gate adj insulating' and ((contact adj hole' near10 (edge or side) near10 (drain adj electrode'))	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:41
190	((semiconductor adj layer) near10 (ohmic adj contact adj layer) near10 (gate adj insulating)	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:29
10	((source and drain) adj electrode) near10 ohmic adj contact adj layer,	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:30
4	((semiconductor adj layer' near10 (ohmic adj contact adj layer' near10 (gate adj insulating)) and (((source and drain) adj electrode) near10 (ohmic adj contact adj layer))	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:53
158	((semiconductor adj layer) near10 (gate adj insulating' near10 above near10 (gate adj electrode'	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 15:10
6	(contact adj hole' near10 over near10 (drain adj electrode) near10 (pixel adj region of area.	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:55
7	contact adj hole' near10 over near10 drain adj electrode' near10 pixel adj region or area	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 14:55
	source and drain adj electrode' near10 opposite adj sides' near10 semiconductor adj layer	USIAT; US-PGPUB; EPC; JPC; DERWENT; IBM_TDB	2003/03/14 15:11

-	30	Source and drain adj electrode near10 semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	4	semiconductor adj layer near10 gate adj insulating near10 above near10 gate adj electrode and source and drain adj electrode near10 semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	20	drain adj electrode near10 reduced near10 side area	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	4	contact adj hole near10 edge of side near10 drain adj electrode and drain adj electrode near10 reduced near10 side area	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	30	contact adj hole near10 drain adj electrode near10 pixel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	4	contact adj hole near10 over near10 drain adj electrode near10 over near10 pixel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	3067	contact adj hole near10 (passivation) near10 expos66 (drain adj electrode) near10 (insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	20	contact adj hole near10 (passivation) near10 expos66 near10 (drain adj electrode) near10 (insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	9	contact adj hole near10 formed near10 over near10 (drain and pixel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 09:50
-	1	6532050.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 09:50